Product data sheet

1. General description

Dual N-channel enhancement mode Field-Effect Transistor (FET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Logic-level compatible
- Very fast switching
- · Trench MOSFET technology
- AEC-Q101 qualified

3. Applications

- Relay driver
- · High-speed line driver
- Low-side load switch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit		
Per transistor	Per transistor								
V _{DS}	drain-source voltage	T _{amb} = 25 °C		-	-	60	V		
V_{GS}	gate-source voltage			-20	-	20	V		
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	-	320	mA		
Static characte	Static characteristics								
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 500 mA; T_j = 25 °C		-	1	1.6	Ω		

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source 1		D ₁ D ₂
2	G1	gate 1	6 5 4	
3	D2	drain 2		
4	S2	source 2		
5	G2	gate 2	∐1 ∐2 ∐3	$\begin{bmatrix} & & & & & & \\ & & & & & & \\ & & & & & $
6	D1	drain 1	TSSOP6 (SOT363)	msd901

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
2N7002HS		plastic, surface-mounted package; 6 leads; 0.65 mm pitch; 2.1 mm x 1.25 mm x 0.95 mm body	SOT363			

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
2N7002HS	C7%

[1] % = placeholder for manufacturing site code

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transiste	or					
V _{DS}	drain-source voltage	T _{amb} = 25 °C		-	60	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	320	mA
		V _{GS} = 10 V; T _{amb} = 100 °C	[1]	-	200	mA
I _{DM}	peak drain current	T _{amb} = 25 °C; single pulse; t _p ≤ 10 μs		-	1.2	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	280	mW
			[1]	-	320	mW
		T _{sp} = 25 °C		-	960	mW
Per device	'			-		_
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	420	mW
T _j	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain	n diode		'	'		'
I _S	source current	T _{amb} = 25 °C	[1]	-	320	mA
	The state of the s	The state of the s				

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

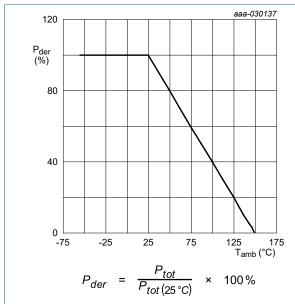


Fig. 1. Normalized total power dissipation as a function of ambient temperature

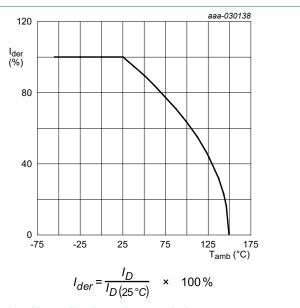


Fig. 2. Normalized continuous drain current as a function of ambient temperature

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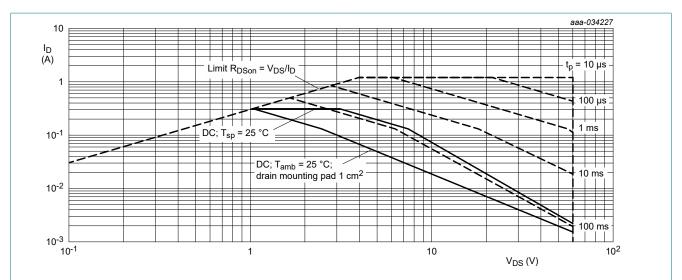


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per device			,				
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	300	K/W
Per transist	or		,	'		'	
R _{th(j-a)}	thermal resistance from	in free air	[1]	-	390	445	K/W
	junction to ambient		[2]	-	340	390	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	130	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

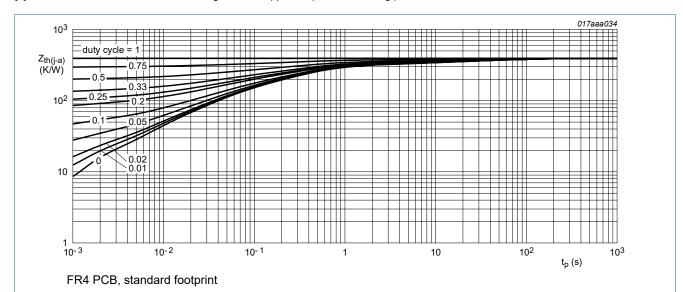


Fig. 4. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

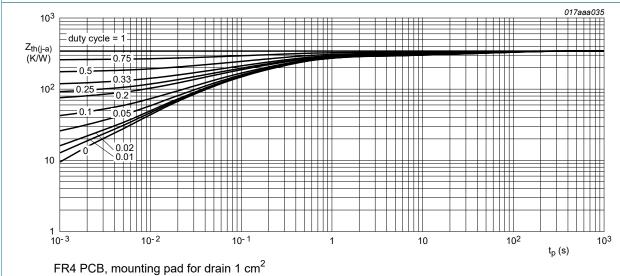


Fig. 5. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = 10 \mu A; V_{GS} = 0 V; T_j = 25 °C$	60	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	1.1	1.75	2.4	V
I _{DSS}	drain leakage current	V _{DS} = 60 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μΑ
		V _{DS} = 60 V; V _{GS} = 0 V; T _j = 150 °C	-	-	10	μΑ
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-100	nA
R _{DSon} drain-source on-state resistance		V_{GS} = 10 V; I_{D} = 500 mA; T_{j} = 25 °C	-	1	1.6	Ω
	resistance	V _{GS} = 10 V; I _D = 500 mA; T _j = 150 °C	-	2.1	3.3	Ω
	$V_{GS} = 5 \text{ V}; I_D = 50 \text{ mA}; T_j = 25 \text{ °C}$	-	1.3	2	Ω	
9 _{fs}	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 200 \text{ mA}; T_j = 25 \text{ °C}$	-	400	-	mS
Dynamic ch	aracteristics			_		
Q _{G(tot)}	total gate charge	$V_{DS} = 30 \text{ V}; I_D = 300 \text{ mA}; V_{GS} = 4.5 \text{ V};$	-	0.3	0.5	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	0.1	-	nC
Q _{GD}	gate-drain charge		-	0.1	-	nC
C _{iss}	input capacitance	V _{DS} = 10 V; f = 1 MHz; V _{GS} = 0 V;	-	34	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	7	-	pF
C _{rss}	reverse transfer capacitance		-	4	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 50 \text{ V}; R_L = 250 \Omega; V_{GS} = 10 \text{ V};$	-	2	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	3	-	ns
t _{d(off)}	turn-off delay time	1	-	6	-	ns
t _f	fall time	1	-	4	-	ns
Source-drai	in diode		'			
V_{SD}	source-drain voltage	I _S = 115 mA; V _{GS} = 0 V; T _i = 25 °C	0.47	0.75	1.1	V

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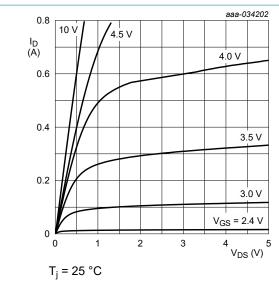


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

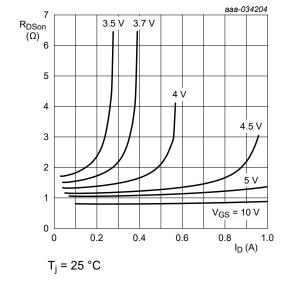


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

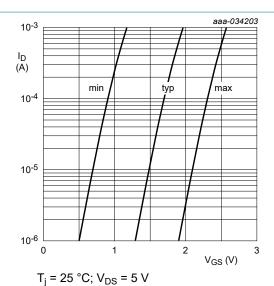


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

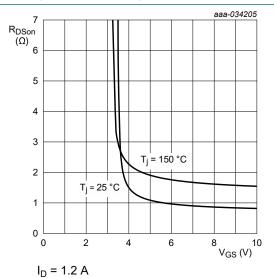


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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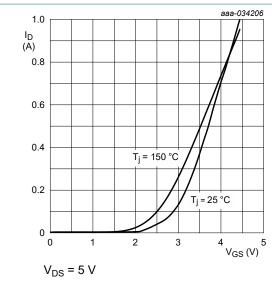


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

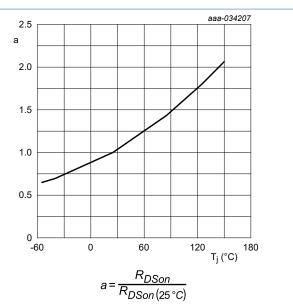


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

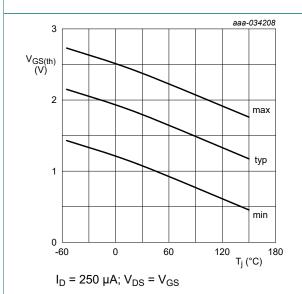
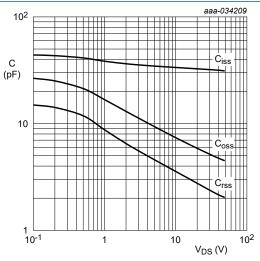


Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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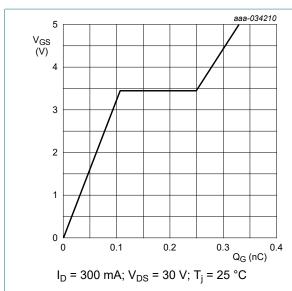


Fig. 14. Gate-source voltage as a function of gate charge; typical values

 $V_{GS} = 0 V$

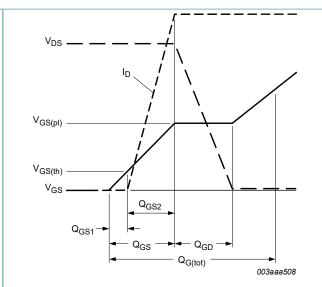


Fig. 15. Gate charge waveform definitions

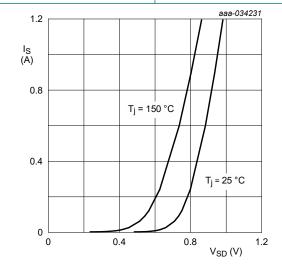
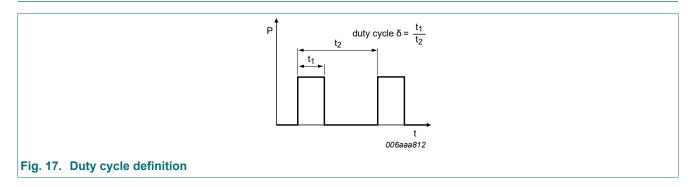


Fig. 16. Source current as a function of source-drain voltage; typical values

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11. Test information



Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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12. Package outline

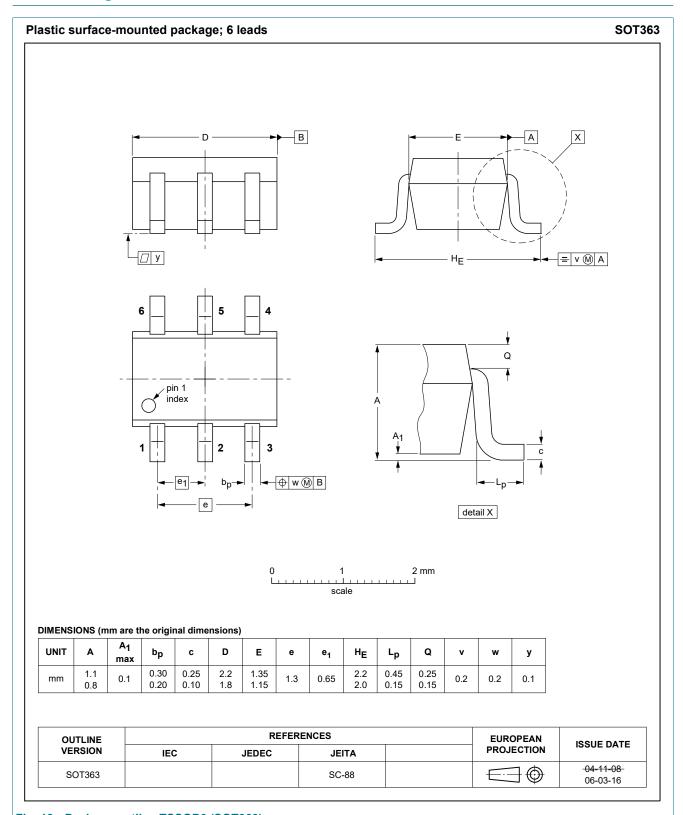
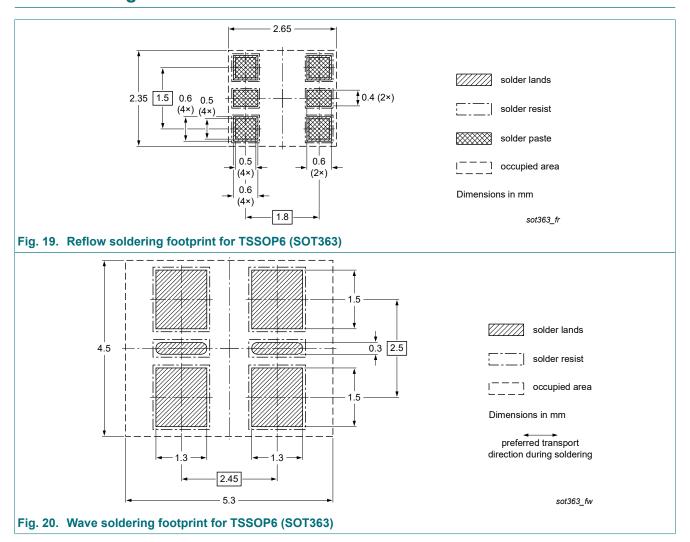


Fig. 18. Package outline TSSOP6 (SOT363)

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13. Soldering



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14. Revision history

Table 8. Revision history

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Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
2N7002HS v.3	20211215	Product data sheet	-	2N7002HS v.2			
Modifications:	Changed values for	Changed values for parameters I _D and I _S					
2N7002HS v.2	20211201	Product data sheet	-	2N7002HS v.1			
2N7002HS v.1	20211119	Preliminary data sheet	-	-			

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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2N7002H

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